2SK2571(Tentative)

Silicon N-Channel Power F-MOS

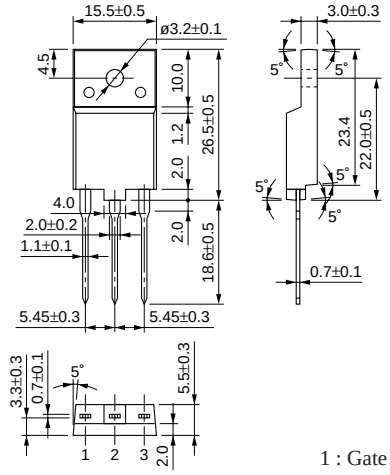
■ Features

- Avalanche energy capability guaranteed
- High-speed switching
- Low ON-resistance
- No secondary breakdown

■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

Unit : mm



1 : Gate
2 : Drain
3 : Source
TOP-3E Package

■ Absolute Maximum Ratings (Tc = 25˚C)

Parameter		Symbol	Rating	Unit
Drain-Source breakdown voltage		V_{DSS}	450	V
Gate-Source voltage		V_{GSS}	±30	V
Drain current	DC	I_D	±13	A
	Pulse	I_{DP}	±26	A
Avalanche energy capability		EAS *	200	mJ
Allowable power dissipation	T_C= 25˚C	P_D	100	W
	Ta= 25˚C		3	
Channel temperature		T_{ch}	150	˚C
Storage temperature		T_{stg}	–55 to +150	˚C

* L= 2.4mH, I_L=13A, 1 pulse

■ Electrical Characteristics (Tc = 25˚C)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	I_{DSS}	V_{DS}= 360V, V_{GS}= 0			100	μ A
Gate-Source leakage current	I_{GSS}	V_{GS}=±30V, V_{DS}= 0			±1	μ A
Drain-Source breakdown voltage	V_{DSS}	I_D=1mA, V_{GS}= 0	450			V
Gate threshold voltage	V_{th}	V_{DS}= 25V, I_D=1mA	2		5	V
Drain-Source ON-resistance	$R_{DS(on)}$	V_{GS}=10V, I_D= 7A		0.34	0.45	Ω
Forward transadmittance	$\|Y_{fs}\|$	V_{DS}= 25V, I_D= 7A	5	8		S
Diode forward voltage	V_{DSF}	I_{DR}=13A, V_{GS}= 0			–2	V
Input capacitance	C_{iss}	V_{DS}= 20V, V_{GS}= 0, f=1MHz		1700		pF
Output capacitance	C_{oss}			300		pF
Feedback capacitance	C_{rss}			120		pF
Turn-on time	t_{on}	V_{DD}≒150V, I_D= 7A V_{GS}=10V, R_L= 21.4Ω		110		ns
Fall time	t_f			90		ns
Turn-off time (delay time)	$t_{d(off)}$			220		ns
Channel-Case heat resistance	$R_{th(ch-c)}$				1.25	˚C/W
Channel-Atmosphere heat resistance	$R_{th(ch-a)}$				41.67	˚C/W